

Abstract Submitted  
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**Polarized spin and valley transport across ferromagnetic silicene junctions** V. VARGIAMIDIS, P. VASILOPOULOS, Concordia University, V. FESSATIDIS, Fordham University — We study ballistic transport of Dirac fermions through silicene barriers, of width  $d$ , with an exchange field  $M$  and metallic gates above them that provide tunable potentials of height  $U$ . Away from the Dirac point (DP) the spin- and valley-resolved conductances, as functions of  $U$ , exhibit resonances and close to it a pronounced dip that becomes a transport gap when an appropriate electric field  $E_z$  is applied. The charge conductance  $g_c$  of such a junction changes from oscillatory to a monotonically decreasing function of  $d$  beyond a critical  $E_z$ . This tuning of  $g_c$  can be used to realize electric-field-controlled switching. Further, the field  $M$  splits each resonance of  $g_c$  in two spin-resolved peaks. The spin polarization  $p_s$  of the current near the DP increases with  $E_z$  or  $M$  and becomes nearly perfect above certain of their values. We also show that  $p_s$  can be inverted either by varying  $U$  or by reversing the direction of  $M$ . For two barriers there is no splitting in  $g_c$  when the fields  $M$  are in opposite directions. Most of these phenomena have no analogs in graphene.

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